U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE ATTY. DOCKET NO. APPLN. NO. ELM/002 Cont. 4 10/672,961 CONF. NO. **APPLICANTS** 9439 Glenn J. Leedy **FILING DATE** 

SEP 2 3 2004

NFORMATION DISCLOSURE ATEMENT BY APPLICANT

> September 26, 2003 2811

**GROUP ART UNIT** 

**U.S. PATENT DOCUMENTS** 

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
mL	2,915,722	12/01/59	Foster	336	115	
1	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	
	3,602,982	09/07/71	Emmasingel	29	577	
	3,615,901	10/26/71	Medicus	148	11.5 R	
	3,716,429	02/13/73	Napoli et al.	156	17	
	3,777,227	12/14/73	Krishna et al.	257	578	
	3,868,565	02/25/75	Kuipers	324	207.26	
	3,922,705	11/25/75	Yerman	357	26	
	3,997,381	12/14/76	Wanlass	156	3	
	4,070,230	01/24/78	Stein	156	657	
	4,131,985	01/02/79	Greenwood et al.	29	580	
	4,142,004	02/27/79	Hauser, Jr. et al.	438	792	·
	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	
	4,401,986	08/30/83	Trenkler et al.	340	870.32	
	4,416,054	11/22/83	Thomas et al.	29	572	<del></del>
	4,500,905	02/19/85	Shibata	357	68	
	4,539,068	09/03/85	Takagi et al.	156	614	
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
MU	4,663,559	05/05/87	Christensen	313	336	

EXAMINER

**DATE CONSIDERED** 

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.

# U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO. ELM/002 Cont. 4	<b>APPLN. NO.</b> 10/672,961
APPLICANTS	CONF. NO.
Glenn J. Leedy	9439
FILING DATE	GROUP ART UNIT
September 26, 2003	2811

### **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MIC	4,684,436	08/04/87	Burns et al.	216	65	
<del></del>	4,693,770	09/15/87	Hatada	156	151	
	4,702,336	10/27/87	Maeda et al.	180	197	-
7	4,702,936	10/27/87	Seibert et al.	427	583	
	4,706,166	11/10/87	Go	361	403	
	4,721,938	01/26/88	Stevenson	338	4	
	4,761,681	08/02/88	Reid	357	68	
	4,784,721	11/15/88	Holmen et al.	156	647	
	4,810,673	03/07/89	Freeman	438	386	
	4,825,277	04/25/89	Mattox et al.	257	639	
	4,857,481	08/15/89	Tam et al.	438	619	
	4,892,753	01/09/90	Wang, et al.	427	579	
	4,897,708	01/30/90	Clements	257	690	
/	4,924,589	05/15/90	Leedy	438	6	
W	4,939,568	07/03/90	Kato, et al.	357	75	
M	4,940,916	07/10/90	Borel et al.	313	306	
	Re B14,940,916	11/26/90	Borel et al.	315	306	
MC	4,950,987	08/21/90	Vranish et al.	324	207.23	
	4,952,446	08/18/90	Lee et al.	428	220	
	4,954,865	09/04/90	Rokos	257	378	
	4,957,882	09/18/90	Shinomiya	438	65	
	4,965,415	10/23/90	Young et al.	200	83 N	
	4,966,663	10/30/90	Mauger	205	656	
	4,983,251	01/08/91	Haisma et al.	438	3	
	4,994,735	02/19/91	Leedy	324	158	
1	5,000,113	03/19/91	Wang, et al.	118	723	
<u></u>	5,008,619	04/16/91	Keogh et al.	324	207.17	
$\overline{M}$	5,010,024	04/23/91	Allen et àl.	438	659	

**EXAMINER** 

**DATE CONSIDERED** 

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609;/Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.

### U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

### INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO.	APPLN. NO.
ELM/002 Cont. 4	10/672,961
APPLICANTS	CONF. NO.
Glenn J. Leedy	9439
FILING DATE September 26, 2003	GROUP ART UNIT 2811

#### **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MC	5,020,219	06/04/91	Leedy	29	846	
	5,034,685	07/23/91	Leedy	324	158 F	
	5,070,026	12/03/91	Greenwald et al.	437	3	
	5,071,510	12/10/91	Findler et al.	156	647	
	5,098,865	03/24/92	Machado et al.	438	788	
	5,103,557	04/14/92	Leedy	29	832	
	5,110,373	05/05/92	Mauger	148	33.2	
	5,111,278	05/05/92	Eichelberger	357	75	
	5,116,777	05/26/92	Chan et al.	438	234	
	5,130,894	07/14/92	Miller	361	393	
	5,132,244	07/21/92	Roy	438	477	
	5,151,775	09/29/92	Hadwin	357	80	<u>.</u>
	5,156,909	10/20/92	Henager, Jr. et al.	428	334	
	5,203,731	04/20/93	Zimmerman	445	24	
	5,225,771	07/06/93	Leedy	324	158	
	5,236,118	08/17/93	Bower et al.	228	193	
	5,240,458	08/31/93	Linglain, et al.	464	63	
	5,259,247	11/09/93	Bantien	73	718	
	5,262,351	11/16/93	Bureau et al.	437	183	
	5,270,261	12/14/93	Bertin et al.	437	209	
	5,273,940	12/28/93	Sanders	437	209	
	5,274,270	12/28/93	Tuckerman	257	758	
	5,279,865	01/18/94	Chebi et al.	427	574	
	5,284,796	02/08/94	Nakanishi et al.	437	183	
	5,323,035	06/21/94	Leedy	257	48	
17	5,324,687	06/28/94	Wojnarowski	437	225	
M	5,354,695	10/11/94	Leedy	438	411	

**EXAMINER** 

**DATE CONSIDERED** 

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609! Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.

# U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

### INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO. ELM/002 Cont. 4	<b>APPLN. NO.</b> 10/672,961
APPLICANTS Glenn J. Leedy	CONF. NO. 9439
FILING DATE September 26, 2003	GROUP ART UNIT

#### **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MC	5,363,021	11/08/94	MacDonald	315	366	
٠ ٦	5,385,632	01/31/95	Goossen	156	630	
	5,385,909	01/31/95	Nelson et al.	514	291	
	RE 34,893	04/04/95	Fujii et al.	257	419	
	5,420,458	05/30/95	Shimoji	257	622	
	5,424,920	06/13/95	Miyake	361	735	
	5,426,072	06/20/95	Finnila	437	208	
	5,426,363	06/20/95	Akagi et al.	324	239	
	5,432,444	07/11/95	Yasohama et al.	324	240	
	5,432,729	07/11/95	Carson et al.	365	63 <sup>-</sup>	-
	5,434,500	07/18/95	Hauck et al.	324	67	
	5,451,489	09/19/95	Leedy	430	313	
	5,453,404	09/26/95	Leedy	437	203	
	5,457,879	10/17/95	Gurtler et al.	29	895	
	5,476,813	12/19/95	Naruse	437	132	
	5,489,554	02/06/96	Gates	437	208	
	5,502,667	03/26/96	Bertin et al.	365	51	
	5,512,397	04/30/96	Leedy	430	30	
	5,527,645	06/18/96	Pati et al.	430 .	5	
	5,529,829	06/25/96	Koskenmaki et al.	428	167	
	5,534,465	07/09/96	Frye et al.	437	209	
	5,555,212	09/10/96	Toshiaki et al.	365	200	
	5,563,084	10/08/96	Ramm et al.	437	51	
	5,571,741	11/05/96	Leedy	437	51	
	5,580,687	12/03/96	Leedy	430	5 ·	
	5,581,498	12/03/96	Ludwig et al.	365	63	
ML	-5,582,939	12/10/96	Pierrat	430	5	

**EXAMINER** 

**DATE CONSIDERED** 

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609 Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ELM/002 Cont. 4	<b>APPLN. NO.</b> 10/672,961	
	IFORMATION DISCLOSURE TATEMENT BY APPLICANT	APPLICANTS Glenn J. Leedy  CONF. NO. 9439		
3	TATEMENT BY APPLICANT	FILING DATE September 26, 2003	GROUP ART UNIT 2811	

#### **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ML	5,583,688	12/10/96	Hornbeck	359	291	
	5,592,007	01/07/97	Leedy	257	347	
	5,592,018	01/07/97	Leedy	257	619	
	5,595,933	01/21/97	Heijboer	439	20	
	5,606,186	02/25/97	Noda	257	226	
	5,627,112	05/06/97	Tennant et al.	438	113	
	5,629,137	05/13/97	Leedy	430	313	·
	5,633,209	05/27/97	Leedy	435	228	
	5,637,536	06/10/97	Val	438	686	
	5,654,127	08/05/97	Leedy	430	315	
	5,654,220	08/05/97	Leedy	438	25	
	5,656,552	08/12/97	Hudak et al.	438	15	
	5,675,185	10/07/97	Chen et al.	257	774	
	5,694,588	12/02/97	Ohara et al.	395	566	
	5,725,995	03/10/98	Leedy	430	315	
	5,750,211	05/12/98	Weise et al.	427	579	<del></del>
	5,760,478	06/02/98	Bozso et al.	257	777	
	5,773,152	06/30/98	Okonogi	428	446	
	5,786,116	07/28/98	Rolfson	430	5	
	5,793,115	08/11/98	Zavracky et al.	257	777	
	5,831,280	11/03/98	Ray	257	48	
	5,834,334	11/10/98	Leedy	438	107	
	5,840,593	11/24/98	Leedy	438	6	
	5,856,695	01/05/99	Ito et al.	257	370	
	5,868,949	02/09/99	Sotokawa et al.	216	18	
	5,869,354	02/09/99	Leedy	438	110	
	5,870,176	02/09/99	Sweatt et al.	355	53	
mu	5,880,010	03/09/99	Davidson	438	455	

**EXAMINER** 

**DATE CONSIDERED** 

EXAMINER: Initial in citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO. ELM/002 Cont. 4	<b>APPLN. NO.</b> 10/672,961
APPLICANTS Glenn J. Leedy	CONF. NO. 9439
FILING DATE September 26, 2003	GROUP ART UNIT 2811

#### **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MC	5,882,532	03/16/99	Field et al.	216	2	
	5,902,118	05/11/99	Hübner	438	106	
	5,915,167	06/22/99	Leedy	438	108	
	5,946,559	08/31/99	Leedy	438	157	
	5,985,693	11/16/99	Leedy	438	107	
	5,998,069	12/07/99	Cutter et al.	430	5	
	6,008,126	12/28/99	Leedy	438	667	
	6,020,257	02/01/00	Leedy	438	626	
	RE 36,623	03/21/00	Wang, et al.	427	579	
	6,045,625	04/04/00	Houston	148	33.3	
	6,084,284	07/04/00	Adamic, Jr.	257	506	
	6,087,284	07/11/00	Brix, et al.	501	69	
	6,097,096	08/01/00	Gardner et al.	257	777	
	6,133,640	10/17/00	Leedy	257	778	
	6,194,245 B1	02/27/01	Tayanaka	438	57	
	6,197,456 B1	03/06/01	Aleshin et al.	430	5	
	6,208,545 B1	03/27/01	Leedy	365	51	
	6,236,602 B1	05/22/01	Patti	365	201	
	6,261,728 B1	07/17/01	Lin	430	30	
	6,288,561 B1	09/11/01	Leedy	324	760	
	6,294,909 B1	09/25/01	Leedy	324	207.17	
$\overline{M}$	6,518,073	02/11/03	Momohara	438	4	12/10/2001

### **FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
	NUMBER					YES	NO
	DE 32 33 195	03/1983	Germany				
MI	JP 60-74643	04/1985	Japan				
701	JP S60-126871	07/1985	Japan				

**EXAMINER** 

DATE CONSIDERED

EXAMINER: Initial it citation considered, whether or not citation is in conformance with MPEP 609; Braw lihe through citation if not conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ELM/002 Cont. 4	APPLN. NO. 10/672,961 CONF. NO. 9439	
	NFORMATION DISCLOSURE	APPLICANTS Glenn J. Leedy		
5	STATEMENT BY APPLICANT	FILING DATE September 26, 2003	GROUP ART UNIT	

#### **FOREIGN PATENT DOCUMENTS**

V	ED 0 400 070	00/4000	500			
11/	EP 0 189 976	08/1986	EPO			
ML	JP S63-229862	09/1988	Japan			
	JP H01-199476	09/1988	Japan	•		
	2641129	12/1988	France			
MU	EP 0 314 437	05/1989	EPO			
MC	GB 2,215,168	09/1989	UK			
MC	JP 402027600A	01/1990	Japan			
M	JP 02-082564	03/1990	Japan			
	JP H03-284871	12/1991	Japan			
MU	WO 92/03848	03/1992	PCT			
MU	JP 04-076946	03/1992	Japan ·			
M	JP 04-083371	03/1992	Japan			
MC	JP 04-107964	04/1992	Japan		·	
MC	JP 04-196263	07/1992	Japan			
M	EP 0 731 525	09/1996	EPO			
MU	WO 98/19337	05/1998	PCT			
M	WO 01/05366	01/2001	PCT			

Aboaf, J.A., "Stresses in SiO<sub>2</sub> Films Obtained from the Thermal Decomposition of Tetraethylorthosilicate – Effect of Heat Treatment and Humidity," J. Electrochem. Soc.: Solid State Science; 116(12): 1732-1736 (Dec. 1969).

Scheuerman, R.J., "Fabrication of Thin Dielectric Films with Low Internal Stresses," J. Vac. Sci. and Tech., 7(1): 143-146 (1970).

Bailey, R., "Glass for Solid-State Devices: Glass film has low intrinsic compressive stress for isolating active layers of magnetic-bubble and other solid-state devices," NASA Tech Brief (1982).

Alloert, K., et al., "A Comparison Between Silicon Nitride Films Made by PCVD of N<sub>2</sub>-SiH<sub>4</sub> /Ar and N<sub>2</sub>-SiH<sub>4</sub>/He," Journal of the Electrochemical Society, Vol. 132, No. 7, pp. 1763-1766, (July 1985).

Nguyen, S.V., "Plasma Assisted Chemical Vapor Deposited Thin Films for Microelectronic Applications, J. Vac. Sci. Technol. Vol. B4, No. 5, pp.1159-1167, (Sep/Oct. 1986).

**EXAMINER** 

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609;/Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.

<b>FORM</b>	PTO-	1449
FURIN	P 1 O-1	1443

## U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO.	APPLN. NO.
ELM/002 Cont. 4	10/672,961
APPLICANTS	CONF. NO.
Glenn J. Leedy	9439
FILING DATE September 26, 2003	GROUP ART UNIT 2811

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
EXAMINER INITIAL	
ML	Wolf, Stanley, "Basics of Thin Films," Silicon Processing for the VLSI Era, pp. 115, 192, 193, and 199 (1986).
MV	Knolle, W.R., et al., "Characterization of Oxygen-Doped, Plasma-Deposited Silicon Nitride," Journal of the Electrochemical Society, Vol. 135, No. 5, pp. 1211-1217, (May 1988).
M	Olmer, et al., "Intermetal Dielectric Deposition by Plasma Enhanced Chemical Vapor Deposition," Fifth IEEE/CHMT International Electronic Manufacturing Technology Symposium - Design-to-Manufacturing Transfer Cycle," pp. 98-99 (1988).
MU	"Partitioning Function and Packaging of Integrated Circuits for Physical Security of Data," IBM Technical Disclosure Bulletin, IBM Corp.; 32(1): 46-49 (June 1989).
MU	Hsieh, et al., "Directional Deposition of Dielectric Silicon Oxide by Plasma Enhanced TEOS Process," 1989 Proceedings, Sixth International IEEE VLSI Multilevel Interconnection Conference, pp. 411-415 (1989).
MU	Runyan,W.R., "Deposition of Inorganic Thin Films," Semiconductor Integrated Circuit Processing Technology, p. 142 (1990).
W	Hendricks, et al., "Polyquinoline Coatings and Films: Improved Organic Dielectrics for IC's and MCM's," Eleventh IEEE/CHMT International Electronics Manufacturing Technology Symposium," pp. 361-265 (1991).
MU	Tessier, et al., "An Overview of Dielectric Materials for Multichip Modules," SPE, Electrical & Electronic Div.; (6): 260-269 (1991).
M	Treichel, et al., "Planarized Low-Stress Oxide/Nitride Passivation for ULSI Devices," J. Phys IV, Colloq. (France), 1 (C2): 839-846 (1991).
M	Vossen, John L., "Plasma-Enhanced Chemical Vapor Deposition," Thin Film Processes II, pp. 536-541 (1991).
MV	Sze, S.M., "Surface Micromachining," Semiconductor Sensors, pp. 58-63 (1994).
$\sqrt{M}$	Krishnamoorthy, et al., "3-D Integration of MQW Modulators Over Active Submicron CMOS Circuits: 375 Mb/s Transimpedance Receiver –Transmitter Circuit," IEEE Photonics Technology Letters, 2(11): 1288-1290 (November 1995).
MV	Tielert, et al., "Benefits of Vertically Stacked Integrated Circuits for Sequential Logic," IEEE, XP-000704550, 121-124 (December 5, 1996).
M	"IC Tower Patent: Simple Technology Receives Patent on the IC Tower, a Stacked Memory Technology," http://www.simpletech.com/whatsnew/memory/@60824.htm (1998).
M	"Miniature Electron Microscopes Without Vacuum Pumps, Self-Contained, Microfabricated Devices with Short Working Distances, Enable Operation in Air," NASA Tech Briefs, 39-40 (1998).
	Partial European Search Report for Application No. EP 02009643 (October 8, 2002).

**EXAMINER** 

**DATE CONSIDERED** 

EXAMINER: Initial of considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.